



3CD100

PNP Silicon Low Frequency High Power Transistor



Features:

1. Heavy output current.Small saturation voltage drop. Good temperature stability.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611.
3. Use for power amplify, Low-speed switch, power adjustment.
4. Quality Class: JP, JT, JCT, GS, G, G+.

TECHNICAL DATA:

(Ta = 25°C)

Parameter name	Symbols	Unit	Specifications								Test Condition
			A	B	C	D	E	F	G	H	
Collector-Emitter Voltage	V _{CEO}	V	30	50	80	110	150	200	250	300	
Emitter-Base Voltage	V _{EBO}	V	4								
Max. Collector Current	I _{CM}	A	10								
Max. Collector Dissipation	P _{CM}	W	100								(Tc:75°C)
Junction Temperature	T _{jm}	°C	175								
Storage Temperature	T _{stg}	°C	-55~+175								
Collector-Emitter Leakage Current	I _{CEO}	mA	3.0								V _{CE} =50V
Collector- Emitter Saturation Voltage Drop	V _{CE(sat)}	V	2.0								A~E: I _C =5A, I _B =1A
											F~H: I _C =2.5A, I _B =0.5A
DC Current Gain	h _{FE}		Max.:180				Min.:7				A~E: V _{CE} =5V, I _C =5A
											F~H: V _{CE} =5V, I _C =2.5A
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	V	A	B	C	D	E	F	G	H	I _C =5mA
			30	50	80	110	150	200	250	300	
E-Base Breakdown Voltage	V _{(BR)EBO}	V	4								I _E =7mA

h_{FE} Colored:

Color	Brown	Red	Orange	Yellow	Green	Blue	Purple
h _{FE}	7~15	15~25	25~40	40~55	55~80	80~120	120~180

Outline and Dimensions: